

CSD13306W Information



For Reference Only

Part Number CSD13306W
Manufacturer Texas Instruments

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 12V 3.5A

Package 6-UFBGA, DSBGA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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CSD13306W Specifications

Manufacturer Part Number CSD13306W Manufacturer Texas Instruments Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 6-UFBGA, DSBGA Series NexFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 12V Current - Continuous Drain (Id) @ 25°C 3.5A (Ta) Drive Voltage (Max Rds On, Min Rds On) 2.5V, 4.5V Vgs(th) (Max) @ Id 1.3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 11.2nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 1370pF @ 6V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 1.9W (Ta) Rds On (Max) @ Id, Vgs 10.2 mOhm @ 1.5A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-DSBGA (1x1.5) Package / Case 6-UFBGA, DSBGA		
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Package6-UFBGA, DSBGASeriesNexFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)12VCurrent - Continuous Drain (Id) @ 25°C3.5A (Ta)Drive Voltage (Max Rds On, Min Rds On)2.5V, 4.5VVgs(th) (Max) @ Id1.3V @ 250μAGate Charge (Qg) (Max) @ Vgs11.2nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds1370pF @ 6VVgs (Max)±10VFET Feature-Power Dissipation (Max)1.9W (Ta)Rds On (Max) @ Id, Vgs10.2 mOhm @ 1.5A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-DSBGA (1x1.5)Package / Case6-UFBGA, DSBGA	Category	Discrete Semiconductor Products
Series NexFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 12V Current - Continuous Drain (Id) @ 25°C 3.5A (Ta) Drive Voltage (Max Rds On, Min Rds On) 2.5V, 4.5V Vgs(th) (Max) @ Id 1.3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 11.2nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 1370pF @ 6V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 1.9W (Ta) Rds On (Max) @ Id, Vgs 10.2 mOhm @ 1.5A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-DSBGA (1x1.5) Package / Case 6-UFBGA, DSBGA		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)12VCurrent - Continuous Drain (Id) @ 25°C3.5A (Ta)Drive Voltage (Max Rds On, Min Rds On)2.5V, 4.5VVgs(th) (Max) @ Id1.3V @ 250μAGate Charge (Qg) (Max) @ Vgs11.2nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds1370pF @ 6VVgs (Max)±10VFET Feature-Power Dissipation (Max)1.9W (Ta)Rds On (Max) @ Id, Vgs10.2 mOhm @ 1.5A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-DSBGA (1x1.5)Package / Case6-UFBGA, DSBGA	Package	6-UFBGA, DSBGA
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)12VCurrent - Continuous Drain (Id) @ 25°C3.5A (Ta)Drive Voltage (Max Rds On, Min Rds On)2.5V, 4.5VVgs(th) (Max) @ Id1.3V @ 250μAGate Charge (Qg) (Max) @ Vgs11.2nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds1370pF @ 6VVgs (Max)±10VFET Feature-Power Dissipation (Max)1.9W (Ta)Rds On (Max) @ Id, Vgs10.2 mOhm @ 1.5A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-DSBGA (1x1.5)Package / Case6-UFBGA, DSBGA	Series	NexFET?
Drain to Source Voltage (Vdss)12VCurrent - Continuous Drain (Id) @ 25°C3.5A (Ta)Drive Voltage (Max Rds On, Min Rds On)2.5V, 4.5VVgs(th) (Max) @ Id1.3V @ 250μAGate Charge (Qg) (Max) @ Vgs11.2nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds1370pF @ 6VVgs (Max)±10VFET Feature-Power Dissipation (Max)1.9W (Ta)Rds On (Max) @ Id, Vgs10.2 mOhm @ 1.5A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-DSBGA (1x1.5)Package / Case6-UFBGA, DSBGA	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 2.5V, 4.5V Vgs(th) (Max) @ Id 1.3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 11.2nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 1370pF @ 6V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10.2 mOhm @ 1.5A, 4.5V Operating Temperature Surface Mount Supplier Device Package Package / Case 3.5A (Ta) 5.5°C ~ 150°C Tolor (Til) Surface Mount Supplier Device Package 6-DSBGA (1x1.5) 6-UFBGA, DSBGA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)2.5V, 4.5VVgs(th) (Max) @ Id1.3V @ 250μAGate Charge (Qg) (Max) @ Vgs11.2nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds1370pF @ 6VVgs (Max)±10VFET Feature-Power Dissipation (Max)1.9W (Ta)Rds On (Max) @ Id, Vgs10.2 mOhm @ 1.5A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-DSBGA (1x1.5)Package / Case6-UFBGA, DSBGA	Drain to Source Voltage (Vdss)	12V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 11.2nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 1370pF @ 6V Vgs (Max) FET Feature - Power Dissipation (Max) 1.9W (Ta) Rds On (Max) @ Id, Vgs 10.2 mOhm @ 1.5A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-DSBGA (1x1.5) Package / Case 6-UFBGA, DSBGA	Current - Continuous Drain (Id) @ 25°C	3.5A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1370pF @ 6V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10.2 mOhm @ 1.5A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-DSBGA (1x1.5) Package / Case 6-UFBGA, DSBGA	Drive Voltage (Max Rds On, Min Rds On)	2.5V, 4.5V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10.2 mOhm @ 1.5A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-DSBGA (1x1.5) Package / Case 6-UFBGA, DSBGA	Vgs(th) (Max) @ Id	1.3V @ 250μA
Vgs (Max)±10VFET Feature-Power Dissipation (Max)1.9W (Ta)Rds On (Max) @ Id, Vgs10.2 mOhm @ 1.5A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-DSBGA (1x1.5)Package / Case6-UFBGA, DSBGA	Gate Charge (Qg) (Max) @ Vgs	11.2nC @ 4.5V
FET Feature - Power Dissipation (Max) 1.9W (Ta) Rds On (Max) @ Id, Vgs 10.2 mOhm @ 1.5A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-DSBGA (1x1.5) Package / Case 6-UFBGA, DSBGA	Input Capacitance (Ciss) (Max) @ Vds	1370pF @ 6V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10.2 mOhm @ 1.5A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-DSBGA (1x1.5) Package / Case 6-UFBGA, DSBGA	Vgs (Max)	±10V
Rds On (Max) @ Id, Vgs10.2 mOhm @ 1.5A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-DSBGA (1x1.5)Package / Case6-UFBGA, DSBGA	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-DSBGA (1x1.5) Package / Case 6-UFBGA, DSBGA	Power Dissipation (Max)	1.9W (Ta)
Mounting Type Surface Mount Supplier Device Package 6-DSBGA (1x1.5) Package / Case 6-UFBGA, DSBGA	Rds On (Max) @ Id, Vgs	10.2 mOhm @ 1.5A, 4.5V
Supplier Device Package 6-DSBGA (1x1.5) Package / Case 6-UFBGA, DSBGA	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 6-UFBGA, DSBGA	Mounting Type	Surface Mount
	Supplier Device Package	6-DSBGA (1x1.5)
Report errors?	Package / Case	6-UFBGA, DSBGA
		Report errors?

CSD13306W Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

CSD13306W Payment Methods



















CSD13306W Shipping Methods













If you have any question about CSD13306W, please do not hesitate to contact us!

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